



VSMF3710

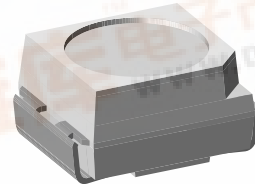
Vishay Semiconductors

High Speed Infrared Emitting Diode, 890 nm RoHS Compliant, Released for Lead (Pb)-free Solder Process

Description

VSMF3710 is a high speed infrared emitting diode in GaAlAs double hetero (DH) technology in a miniature PLCC-2 SMD package.

DH technology combines high speed with high radiant power at wavelength of 890 nm.



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Features

- High radiant power
- High speed: $t_r = 30$ ns
- High modulation band width: $f_c = 12$ MHz
- Peak wavelength: $\lambda_p = 890$ nm
- High reliability
- Low forward voltage
- Suitable for high pulse current application
- Wide angle of half intensity
- Compatible with automatic placement equipment
- EIA and ICE standard package
- 8 mm tape and reel standard: GS08 or GS18
- Lead (Pb)-free reflow soldering
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Applications

- High speed IR data transmission
- High power emitter for low space applications
- High performance transmissive or reflective sensors

Order Instructions

| Part | Ordering code | Remarks |
|----------|---------------|----------------------------------|
| VSMF3710 | VSMF3710-GS08 | MOQ: 7500 pcs, 1500 pcs per reel |
| VSMF3710 | VSMF3710-GS18 | MOQ: 8000 pcs, 8000 pcs per reel |

Absolute Maximum Ratings

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Value | Unit |
|---------------------------------------|---|------------|---------------|------------------|
| Reverse voltage | | V_R | 5 | V |
| Forward current | | I_F | 100 | mA |
| Peak forward current | $t_p/T = 0.5$, $t_p = 100$ μs | I_{FM} | 200 | mA |
| Surge forward current | $t_p = 100$ μs | I_{FSM} | 1 | A |
| Power dissipation | | P_V | 170 | mW |
| Junction temperature | | T_j | 100 | $^\circ\text{C}$ |
| Operating temperature range | | T_{amb} | - 40 to + 85 | $^\circ\text{C}$ |
| Storage temperature range | | T_{stg} | - 40 to + 100 | $^\circ\text{C}$ |
| Soldering temperature | acc. figure 8, J-STD-020B | T_{sd} | 260 | $^\circ\text{C}$ |
| Thermal resistance junction / ambient | | R_{thJA} | 400 | K/W |



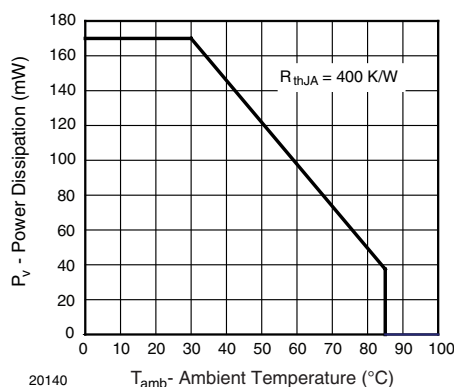


Figure 1. Power Dissipation Limit vs. Ambient Temperature

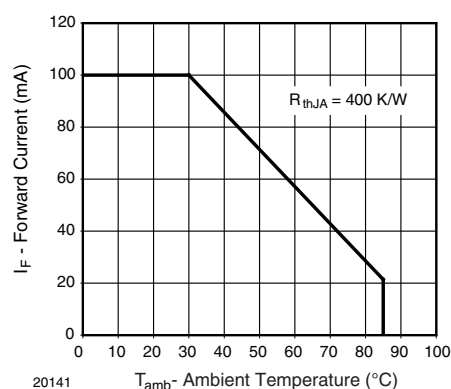


Figure 2. Forward Current Limit vs. Ambient Temperature

Basic Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|----------------------------------|---|------------------|-----|----------|-----|---------------|
| Forward voltage | $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ | V_F | | 1.4 | 1.6 | V |
| | $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$ | V_F | | 2.3 | | V |
| Temp. coefficient of V_F | $I_F = 100\text{ mA}$ | TK_{V_F} | | - 2.1 | | mV/K |
| Reverse current | $V_R = 5\text{ V}$ | I_R | | | 10 | μA |
| Junction capacitance | $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ | C_j | | 125 | | pF |
| Radiant intensity | $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ | I_e | 6 | 10 | 22 | mW/sr |
| | $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$ | I_e | | 100 | | mW/sr |
| Radiant power | $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ | ϕ_e | | 40 | | mW |
| Temp. coefficient of ϕ_e | $I_F = 100\text{ mA}$ | TK_{ϕ_e} | | - 0.35 | | %/K |
| Angle of half intensity | | φ | | ± 60 | | deg |
| Peak wavelength | $I_F = 100\text{ mA}$ | λ_p | | 890 | | nm |
| Spectral bandwidth | $I_F = 100\text{ mA}$ | $\Delta\lambda$ | | 40 | | nm |
| Temp. coefficient of λ_p | $I_F = 100\text{ mA}$ | TK_{λ_p} | | 0.25 | | nm/K |
| Rise time | $I_F = 100\text{ mA}$ | t_r | | 30 | | ns |
| Fall time | $I_F = 100\text{ mA}$ | t_f | | 30 | | ns |
| Virtual source size | | \varnothing | | 0.44 | | mm |



Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

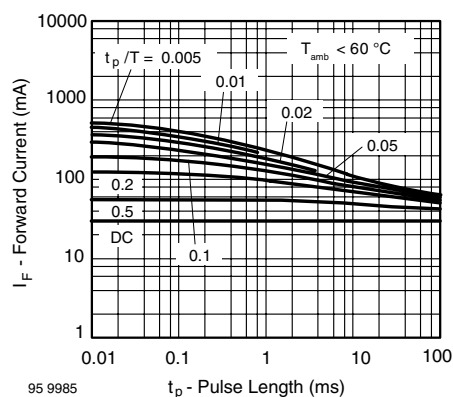


Figure 3. Pulse Forward Current vs. Pulse Duration

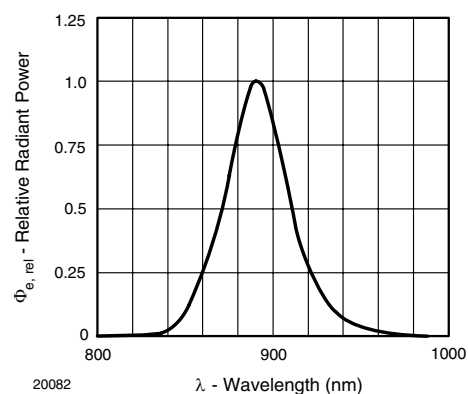


Figure 6. Relative Radiant Power vs. Wavelength

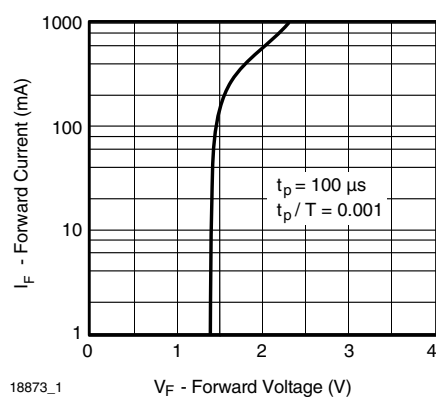


Figure 4. Forward Current vs. Forward Voltage

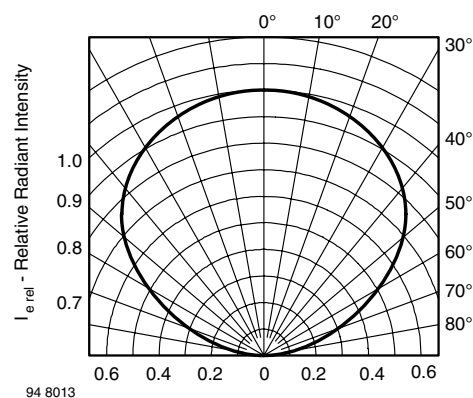


Figure 7. Relative Radiant Intensity vs. Angular Displacement

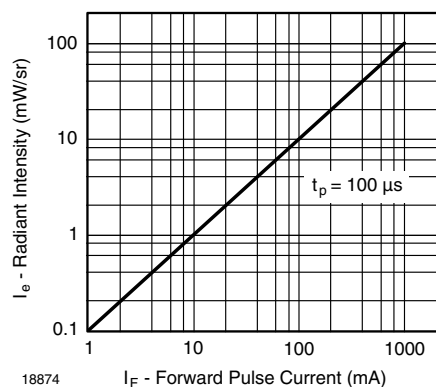


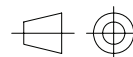
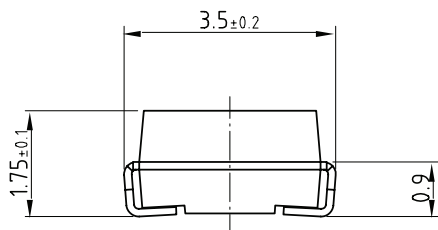
Figure 5. Radiant Intensity vs. Forward Pulse Current

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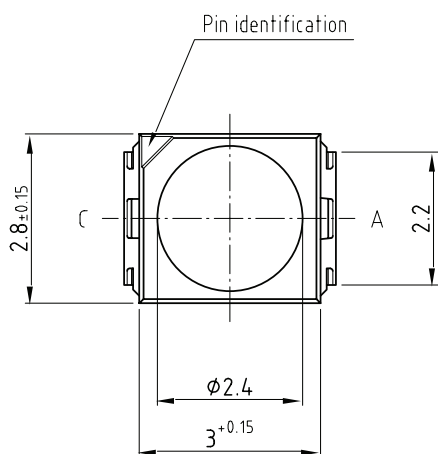


Package Dimensions

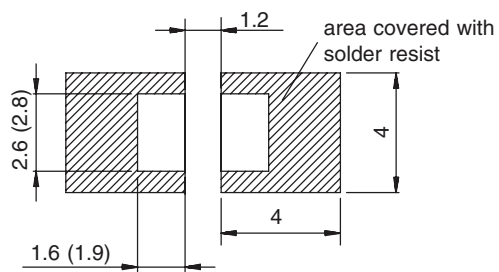


technical drawings
according to DIN
specifications

Dimensions in mm



Mounting Pad Layout



20541_1

Drawing-No.: 6.541-5067.01-4

Issue: 2; 27.06.06

Solder Profile

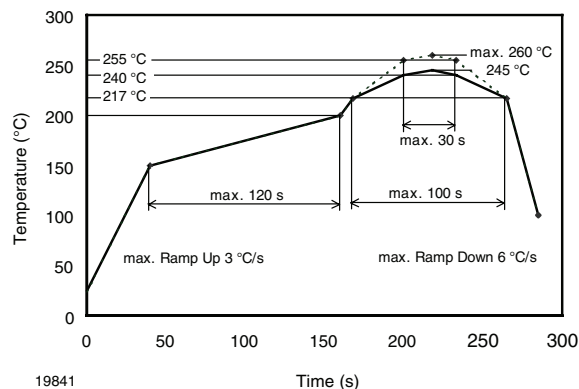


Figure 8. Lead (Pb)-free Reflow Solder Profile acc. J-STD-020B for Preconditioning acc. to JEDEC, Level 2a

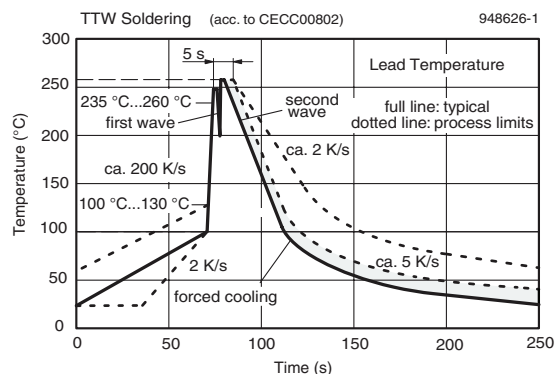


Figure 9. Double Wave Solder Profile for Opto Components

Drypack

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

Floor Life

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor Life: 4 weeks

Conditions: $T_{amb} < 30\text{ °C}$, RH < 60 %

Moisture Sensitivity Level 2a, acc. to J-STD-020B.

Drying

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or Label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 %.

Tape and Reel

PLCC-2 components are packed in antistatic blister tape (DIN IEC (CO) 564) for automatic component insertion. Cavities of blister tape are covered with adhesive tape.

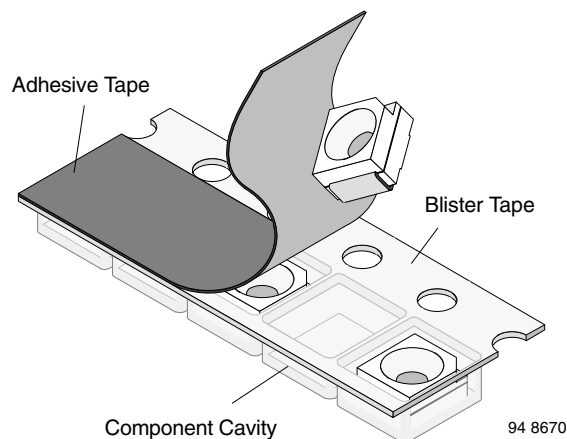


Figure 10. Blister Tape

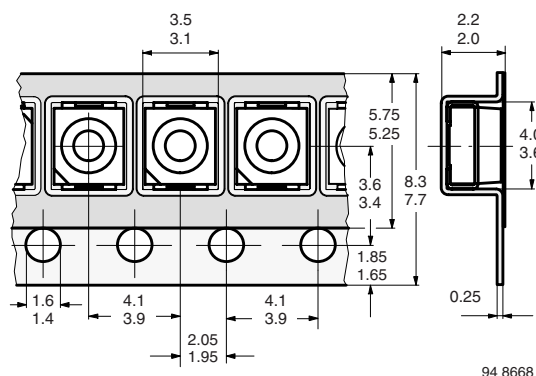


Figure 11. Tape Dimensions in mm for PLCC-2

Missing Devices

A maximum of 0.5 % of the total number of components per reel may be missing, exclusively missing components at the beginning and at the end of the reel. A maximum of three consecutive components may be missing, provided this gap is followed by six consecutive components.

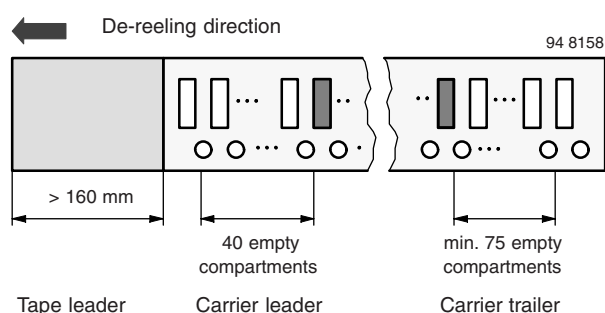


Figure 12. Beginning and End of Reel

The tape leader is at least 160 mm and is followed by a carrier tape leader with at least 40 empty compartments. The tape leader may include the carrier tape as long as the cover tape is not connected to the carrier tape. The least component is followed by a carrier tape trailer with a least 75 empty compartements and sealed with cover tape.

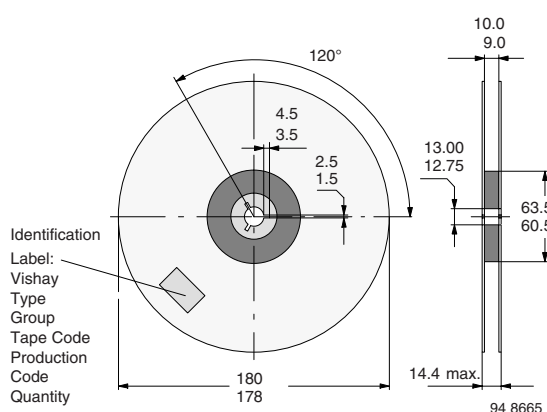


Figure 13. Dimensions of Reel-GS08

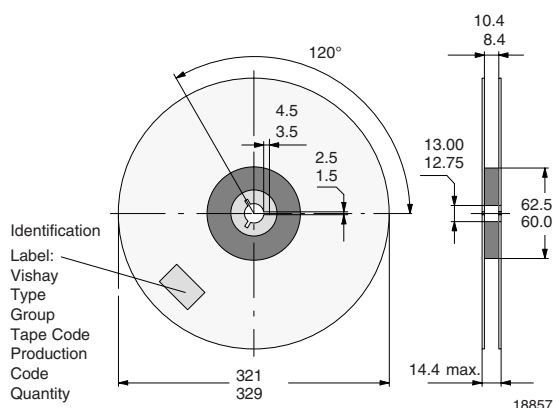


Figure 14. Dimensions of Reel-GS18

Cover Tape Removal Force

The removal force lies between 0.1 N and 1.0 N at a removal speed of 5 mm/s. In order to prevent components from popping out of the blisters, the cover tape must be pulled off at an angle of 180° with regard to the feed direction.



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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